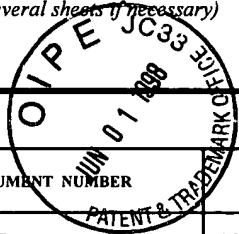


<p style="text-align: center;">INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p>	<p>Docket Number (Optional) 11675.23</p>	<p>Application Number 09/031,617</p>
<p>Applicant(s) Cathey, et al.</p>		
<p>Filing Date 2/27/98</p>		<p>Group Art Unit</p>



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JP	1	5,069,747	12/3/91	Cathey, et al.	156	643	12/21/90

RECEIVED
JUN 15 1998
GROUP 2100

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		NONE						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
JP	2	Verhaar, et al., "A 25 um Bulk Fill CMOS SRAM Cell Technology With Fully Overlapping Contacts," IEDM Technical Digest, pp. 473-476, International Electron Devices Meeting, San Francisco, CA December 9-12, 1990.

<p>EXAMINER </p>	<p>DATE CONSIDERED 11-12-99</p>
-------------------------	--

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.